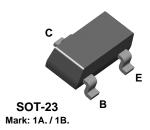
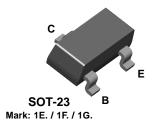


# **BC846A BC846B**

# **BC847A BC847B BC847C**





# **NPN General Purpose Amplifier**

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from 1.0 µA to 50 mA. Sourced from Process 07.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CEO</sub>	Collector-Emitter Voltage	BC846 series	65	V
		BC847 series	45	V
V <sub>CES</sub>	Collector-Base Voltage	BC846 series	80	V
		BC847 series	50	V
V <sub>EBO</sub>	Emitter-Base Voltage		6.0	V
I <sub>C</sub>	Collector Current - Continuous		100	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature	Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BC846 / BC847	
P <sub>D</sub>	Total Device Dissipation	325	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

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(continued)

EIA	ctrice	م ا د	hara	otor	istics
	CUIC	aı C	ılald	10 LEI	12002

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Condit	ions	Min	Max	Units
OFF CHAP	RACTERISTICS					
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown	$I_C = 10 \text{ mA}, I_B = 0$	846A / B	65		V
	Voltage		847A / B	45		
V <sub>(BR)CES</sub>	Collector-Base Breakdown Voltage	$I_C = 10  \mu A, I_E = 0$	846A / B	80		V
			847A / B	50		
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$		6.0		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}$			15	nA
		$V_{CB} = 30 \text{ V}, T_A = 150$		5.0	μΑ	

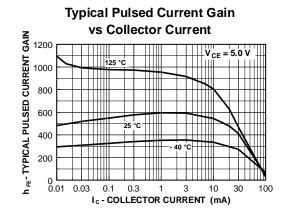
#### **ON CHARACTERISTICS**

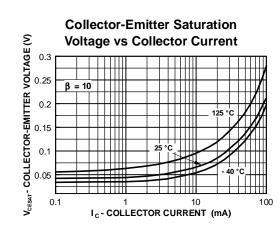
h <sub>FE</sub>	DC Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$			
		846A / 847A	110	220	
		846B / 847B	200	450	
		847C	420	800	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.25	V
		$I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$		0.6	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	0.58	0.70	V
(- )	_	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$		0.77	V

#### SMALL SIGNAL CHARACTERISTICS

f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0,$ f = 100 MHz	100		MHz
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		4.5	pF
NF	Noise Figure	$I_C = 0.2$ mA, $V_{CE} = 5.0$ , $R_S = 2.0$ k $\Omega$ , $f = 1.0$ kHz, BW = 200 Hz		10	dB

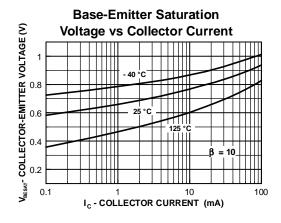
# **Typical Characteristics**

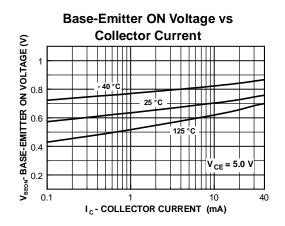




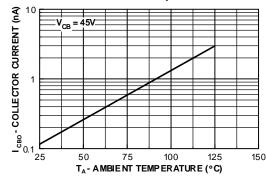
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# **Typical Characteristics**

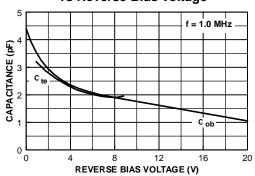




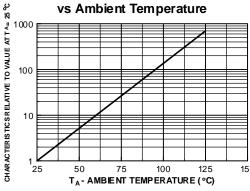
# Collector-Cutoff Current vs Ambient Temperature



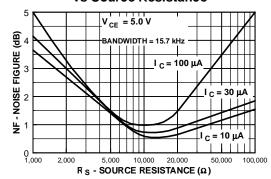
Input and Output Capacitance vs Reverse Bias Voltage



Normalized Collector-Cutoff Current vs Ambient Temperature

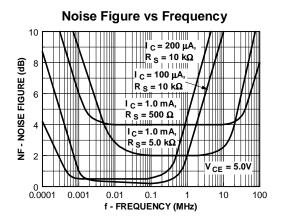


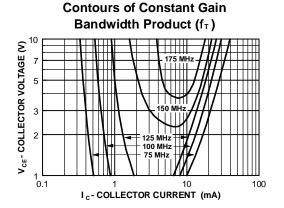
Wideband Noise Frequency vs Source Resistance

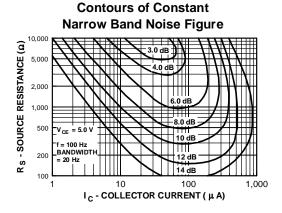


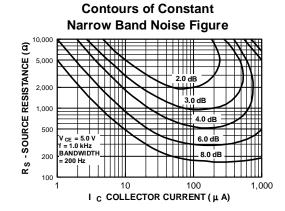
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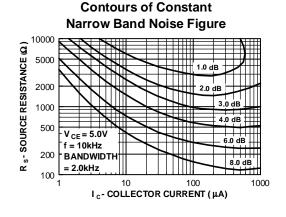
### Typical Characteristics (continued)

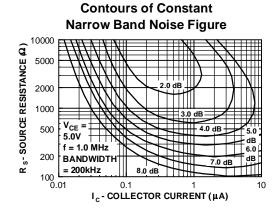








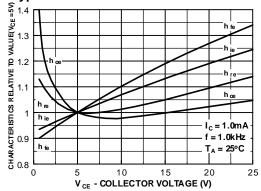




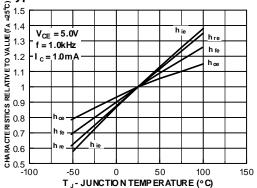
(continued)

# **Typical Common Emitter Characteristics** (f = 1.0 kHz)

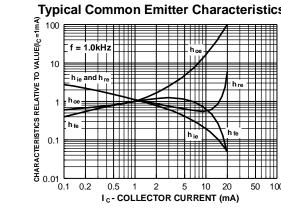
### Typical Common Emitter Characteristics

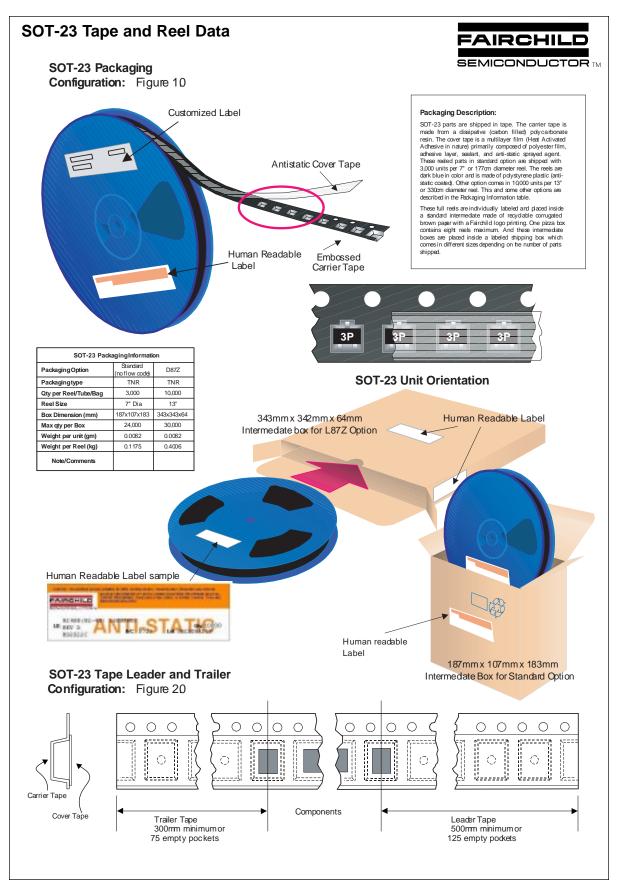


# Typical Common Emitter Characteristics



#### **Typical Common Emitter Characteristics**



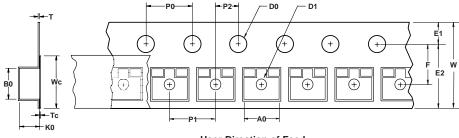


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# SOT-23 Tape and Reel Data, continued

## **SOT-23 Embossed Carrier Tape**

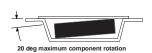
Configuration: Figure 3.0



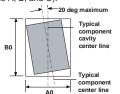
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



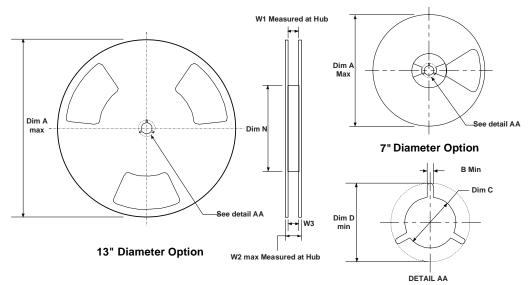
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

### SOT-23 Reel Configuration: Figure 4.0

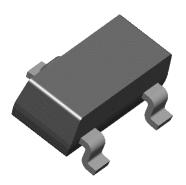


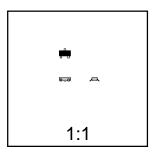
	Dimensions are in inches and millimeters												
Tape Size	Tape Size Reel Option Dim A Dim B		Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)					
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9				
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9				

# **SOT-23 Package Dimensions**



# SOT-23 (FS PKG Code 49)

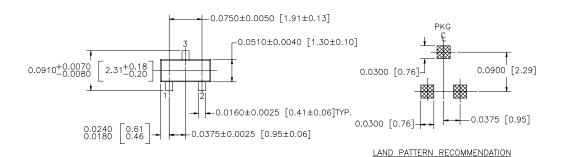


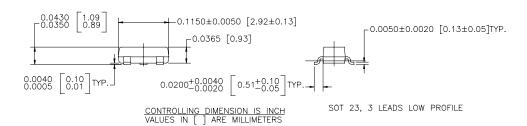


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082



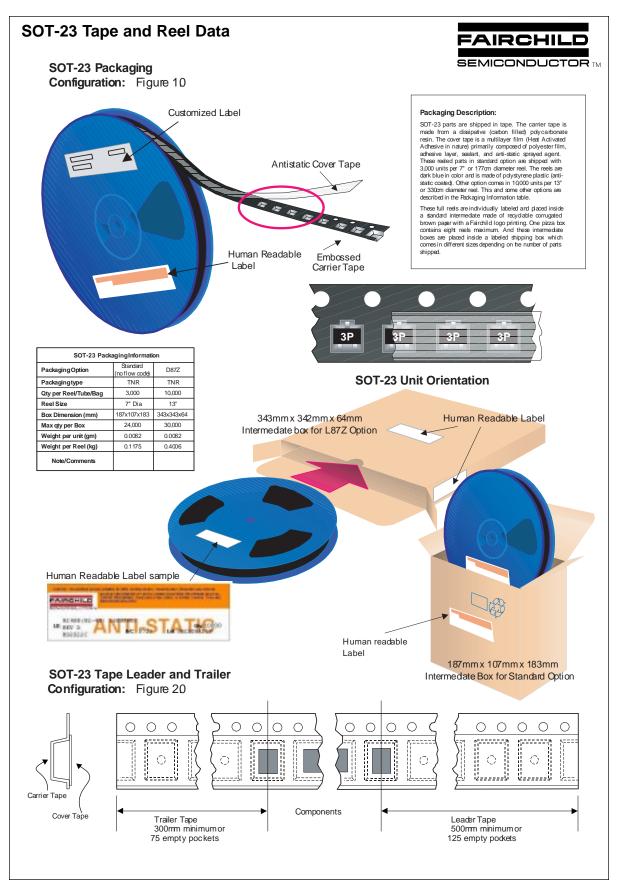


NOTE: UNLESS OTHERWISE SPECIFIED

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- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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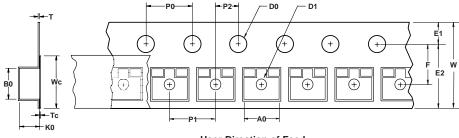


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# SOT-23 Tape and Reel Data, continued

## **SOT-23 Embossed Carrier Tape**

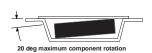
Configuration: Figure 3.0



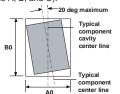
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



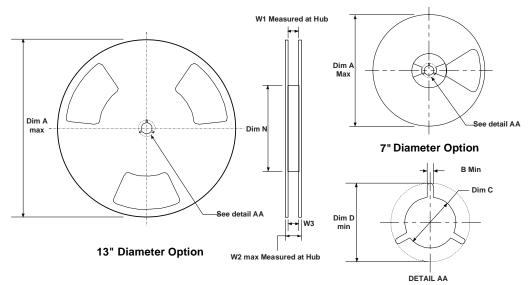
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

### SOT-23 Reel Configuration: Figure 4.0

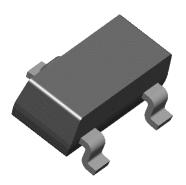


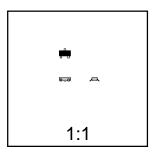
	Dimensions are in inches and millimeters												
Tape Size	Tape Size Reel Option Dim A Dim B		Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)					
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9				
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9				

# **SOT-23 Package Dimensions**



# SOT-23 (FS PKG Code 49)

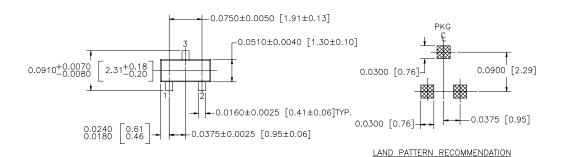


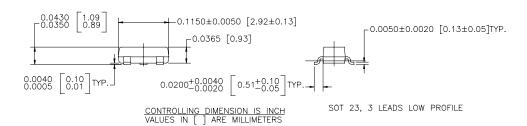


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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Rev. G